ABSTRACT

METHODS AND APPARATUS FOR A HYBRID CAPACITIVELY-COUPLED AND AN INDUCTIVELYCOUPLED PLASMA PROCESSING SYSTEM

A capacitively-coupled plasma (CCP) processing system having a plasma processing chamber for processing a substrate is provided. The capacitively-coupled Plasma (CCP) processing system includes an upper electrode and a lower electrode for processing the substrate, which is disposed on the lower electrode during plasma processing. The capacitively-coupled Plasma (CCP) processing system also includes an array of inductor coils arrangement configured to inductively sustain plasma in a gap between the upper electrode and the lower electrode.

Fig. 3A